

**Silicon PNP Power Transistors**

**2N6490**

**DESCRIPTION**

- With TO-220 package
- Complement to type 2N6487

**APPLICATIONS**

- It is intended for use in power linear and low frequency switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

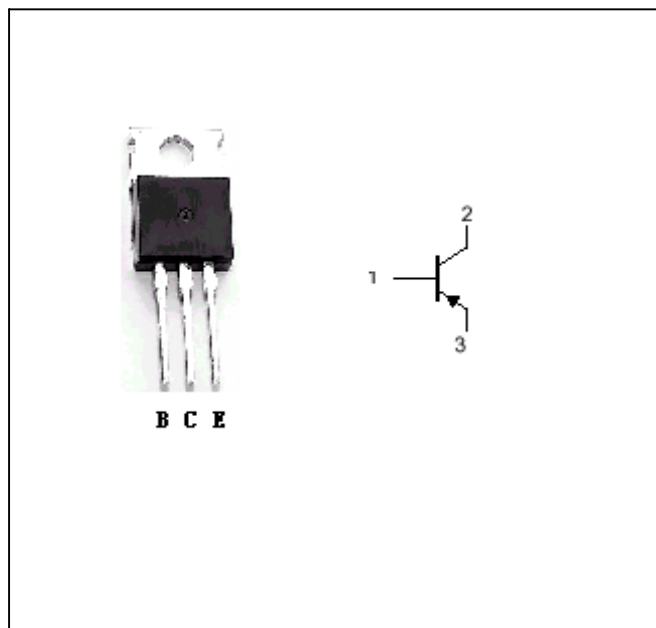


Fig.1 simplified outline (TO-220) and symbol

**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	70	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	60	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		15	A
I <sub>B</sub>	Base current		5	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25	75	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-65~150	

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	1.67	/W

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.2A ; I <sub>B</sub> =0	60			V
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A I <sub>B</sub> =0.5A			1.3	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =15A I <sub>B</sub> =5A			3.5	V
V <sub>BE-1</sub>	Base-emitter on voltage	I <sub>C</sub> =5A ; V <sub>CE</sub> =4V			1.3	V
V <sub>BE-2</sub>	Base-emitter on voltage	I <sub>C</sub> =15A ; V <sub>CE</sub> =4V			3.5	V
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =30V; I <sub>B</sub> =0			1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =4V	20		150	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =15A ; V <sub>CE</sub> =4V	5			

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PACKAGE OUTLINE

